

v00.1115

HMC863ALP4E

GaAs pHEMT MMIC ½ WATT POWER AMPLIFIER, 22 - 26.5 GHz

Typical Applications

The HMC863ALP4E is ideal for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios
- VSAT
- Military & Space

Features

Saturated Output Power: up to +27.5 dBm @ 15% PAE High Output IP3: +33 dBm High Gain: 21.5 dB DC Supply: +6V @ 350mA No External Matching Required

24 Lead 4x4 mm SMT Package: 16 mm²

Functional Diagram



General Description

The HMC863ALP4E is a three stage GaAs pHEMT MMIC ½ Watt Power Amplifier which operates between 22 and 26.5 GHz. The HMC863ALP4E provides 21.5 dB of gain, +27.5 dBm of saturated output power and 15% PAE from a +6V supply. High output IP3 makes the HMC863ALP4E ideal for point-to-point and point-to-multi-point radio systems as well as VSAT applications. The RF I/Os are DC blocked and matched to 50 Ohms for ease of integration into higher level assemblies. The HMC863ALP4E can also be operated from a 5V supply with only a slight decrease in output power & IP3.

Electrical Specifications, $T_A = +25^{\circ}$ C, Vdd = Vdd1 = Vdd2 = +6V, Idd = 350mA^[1]

Parameter	Min.	Тур.	Max.	Units
Frequency Range	22 - 26.5			GHz
Gain	19	21.5		dB
Gain Variation Over Temperature		0.032		dB/ °C
Input Return Loss		11		dB
Output Return Loss		15		dB
Output Power for 1 dB Compression (P1dB)	22	24.5		dBm
Saturated Output Power (Psat)		27		dBm
Output Third Order Intercept (IP3) ^[2]		33		dBm
Total Supply Current (Idd)		350	380	mA

[1] Adjust Vgg between -2 to 0V to achieve Idd = 350mA typical.

[2] Measurement taken at +6V @ 350mA, Pout / Tone = +14 dBm

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Absolute Maximum Ratings

Drain Bias Voltage (Vd)	6.3V	
RF Input Power (RFIN)	+26 dBm	
Channel Temperature	150 °C	
Continuous Pdiss (T= 85 °C) (derate 37 mW/°C above 85 °C)	2.52 W	
Thermal Resistance (channel to ground paddle)	26.9 C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-55 to +85 °C	
ESD Sensitivity (HBM)	Class 0, 150V	

Typical Supply Current vs. Vdd

Vdd (V)	ldd (mA)		
+5.0	350		
+5.5	350		
+6.0	350		

Note: Amplifier will operate over full voltage ranges shown above Vgg adjusted to achieve Idd = 350mA at +5.5V

ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS



6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

7. CLASSIFIED AS MOISTURE SENSITIVITY LEVEL (MSL) 1.